

# PR2001G - PR2007G

## FAST RECOVERY GLASS PASSIVATED RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V CURRENT: 2.0 A

#### **Features**

- Glass Passivated Die Construction
- Diffused Junction
- Fast Switching for High Efficiency
- High Current Capability and Low Forward Voltage Drop
- Surge Overload Rating to 80A Peak
- Low Reverse Leakage Current
- Plastic Material: UL Flammability Classification Rating 94V-0

#### **Mechanical Data**

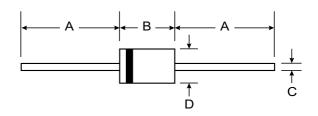
Case: DO-15Molded Plastic

Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208
Polarity: Cathode Band
Marking: Type Number
Weight: 0.4 grams (approx.)







DO-15							
Dim	Min	Max					
Α	25.40	_					
В	5.50	7.62					
С	0.686	0.889					
D	2.60	3.60					
All Dimensions in mm							

### Maximum Ratings and Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

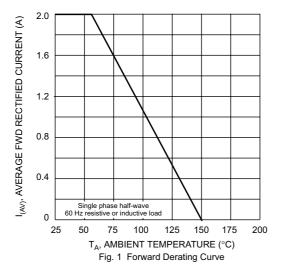
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

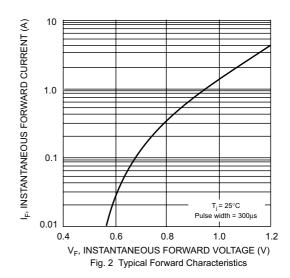
Characteristic		Symbol	PR 2001G	PR 2002G	PR 2003G	PR 2004G	PR 2005G	PR 2006G	PR 2007G	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	50	100	200	400	600	800	1000	٧
RMS Reverse Voltage		V <sub>R(RMS)</sub>	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @ T <sub>A</sub>	= 55°C	Io				2.0				Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load (JEDEC Method)		I <sub>FSM</sub>	80							А
Forward Voltage Drop @ I <sub>F</sub>	= 2.0A	$V_{FM}$	FM 1.3					٧		
1	25°C 100°C	I <sub>RM</sub>	5.0 100						μΑ	
Reverse Recovery Time (Note 3)		t <sub>rr</sub>		15	50		250	50	00	ns
Typical Junction Capacitance (Note 2)		Cj	35							pF
Typical Thermal Resistance Junction to Ambient		$R_{\theta JA}$	50						K/W	
Operating and Storage Temperature Range		T <sub>j</sub> , T <sub>STG</sub>	-65 to +150						°C	

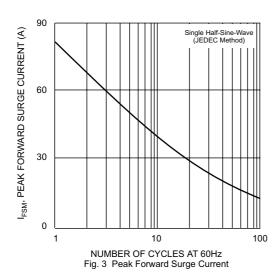
Notes:

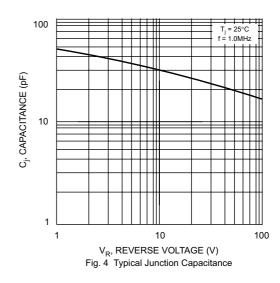
- 1. Valid provided that leads are maintained at ambient temperature at a distance of 9.5mm from the case.
- 2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
- 3. Measured with  $I_F$  = 0.5A,  $I_R$  = 1.0A,  $I_{rr}$  = 0.25A. See figure 5.

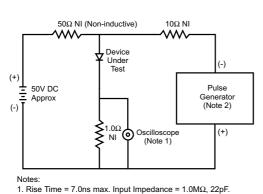


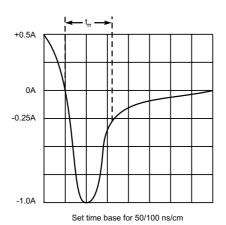












2. Rise Time = 10ns max. Input Impedance =  $50\Omega$ .

Fig. 5 Reverse Recovery Time Characteristic and Test Circuit